

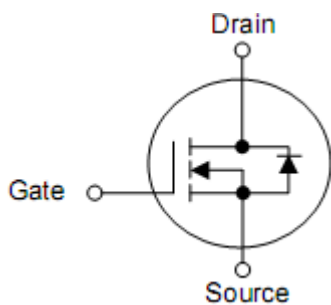
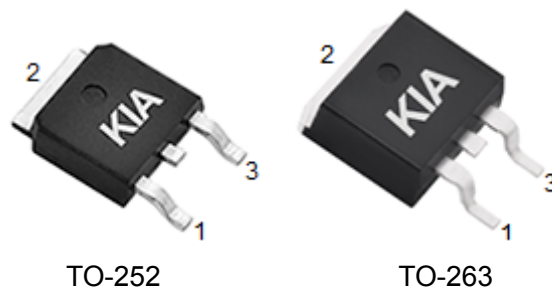
1. Features

- $R_{DS(ON)}=6.5m\Omega(\text{typ.})@V_{GS}=10V$
- Very Low On-resistance $R_{DS(ON)}$
- Low C_{rss}
- Fast switching
- 100% avalanche tested
- Improved dv/dt capability

2. Applications

- PWM Application
- Power Management
- Load switch

3. Symbol



Pin	Function
1	Gate
2	Drain
3	Source

4. Ordering Information

Part Number	Package	Brand
KND3306C	TO-252	KIA
KNB3306C	TO-263	KIA

5. Absolute maximum ratings

$T_C=25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	Rating	Units
Drain-source voltage	V_{DSS}	68	V
Continuous drain current	$T_C=25^\circ\text{C}$ I_D	80	A
	$T_C=100^\circ\text{C}$ I_D	52	A
Pulsed drain current -Pulsed ¹⁾	I_{DM}	320	A
Gate-source voltage	V_{GS}	± 25	V
Single pulse avalanche energy ²⁾	E_{AS}	260	mJ
Power dissipation($T_C=25^\circ\text{C}$)	P_D	125	W
Operating junction and storage temperature range	T_J, T_{STG}	-55 to 150	$^\circ\text{C}$
Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds	T_L	300	$^\circ\text{C}$

*Drain current limited by maximum junction temperature.

6. Thermal characteristics

Parameter	Symbol	Rating	Unit
Thermal resistance junction-case	$R_{\theta JC}$	1	$^\circ\text{C/W}$

7. Electrical characteristics

(T_C=25°C unless otherwise noted)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Units
Drain-source breakdown voltage	BV _{DSS}	V _{GS} =0V, I _D =250uA	68	-	-	V
Drain-source leakage current	I _{DSS}	V _{DS} =68V, V _{GS} =0V	-	-	1	uA
Gate-source forward leakage	I _{GSS}	V _{GS} =±25V, V _{DS} =0V	-	-	±100	nA
Gate threshold voltage	V _{GS(TH)}	V _{DS} =V _{GS} , I _D =250uA	2.0	3.0	4.0	V
Drain-source on-resistance	R _{DS(on)}	V _{GS} =10V, I _D =20A	-	6.5	8.5	mΩ
Input capacitance	C _{iss}	V _{DS} =35V, V _{GS} =0V f=1MHz	-	5850	-	pF
Output capacitance	C _{oss}		-	230	-	pF
Reverse transfer capacitance	C _{rss}		-	210	-	pF
Turn-on delay time	t _{d(on)}	V _{GS} =10V, V _{DS} =35V, R _L =3Ω, I _D =40A, T _J =25°C ³⁾	-	25	-	ns
Rise time	t _r		-	24	-	ns
Turn-off delay time	t _{d(off)}		-	48	-	ns
Fall time	t _f		-	10	-	ns
Total gate charge(10V)	Q _g	V _{DS} =60V, I _D =40A V _{GS} =10V ³⁾	-	92.6	-	nC
Gate-source charge	Q _{gs}		-	23	-	nC
Gate-drain charge	Q _{gd}		-	37	-	nC
Gate Resistance	R _G	f=1MHz	-	3.3	-	Ω
Maximum Continuous Drain-Source Diode Forward Current	I _S	—	-	-	80	A
Maximum Pulsed Drain-Source Diode Forward Current	I _{SM}	—	-	-	320	A
Diode forward voltage	V _{SD}	I _{SD} =20A, V _{GS} =0V, T _J =25°C	-	-	1.2	V

Note:

- 1) Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature
- 2) EAS condition: T_J=25°C, V_{DD}=50V, V_G=10V, L=0.5mH.
- 3) Pulse Test: Pulse Width≤300μs, Duty Cycle≤0.5%

8. Typical operating characteristics

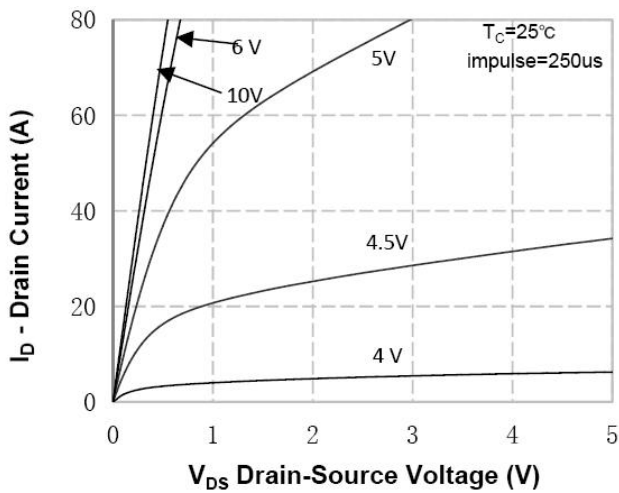


Figure 1. On-Region Characteristics

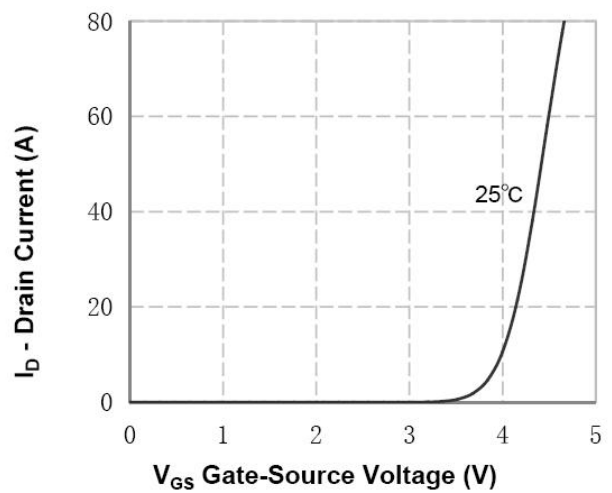


Figure 2. Transfer Characteristics

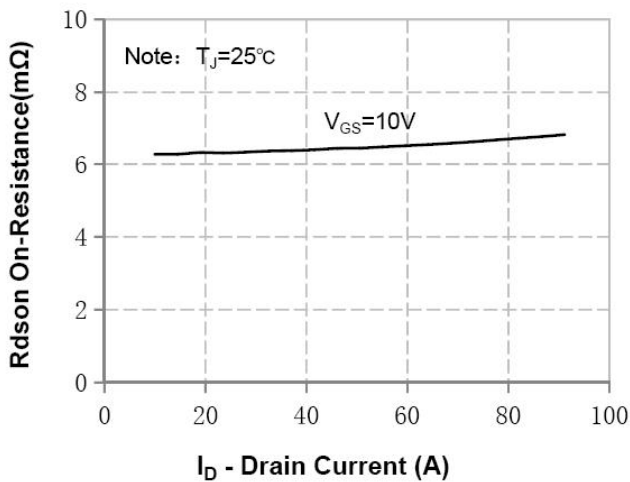


Figure 3. On-Resistance Variation vs Drain Current and Gate Voltage

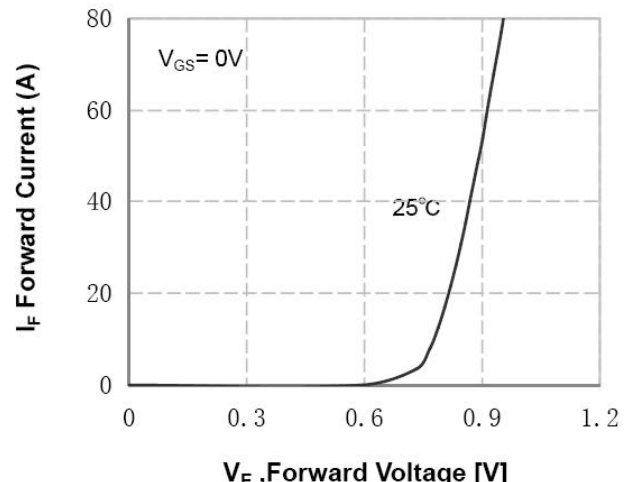


Figure 4. Body Diode Forward Voltage Variation vs Source Current

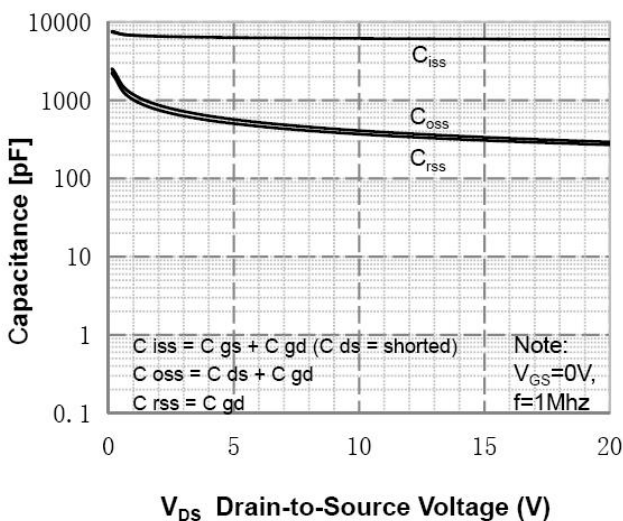


Figure 5. Capacitance Characteristics

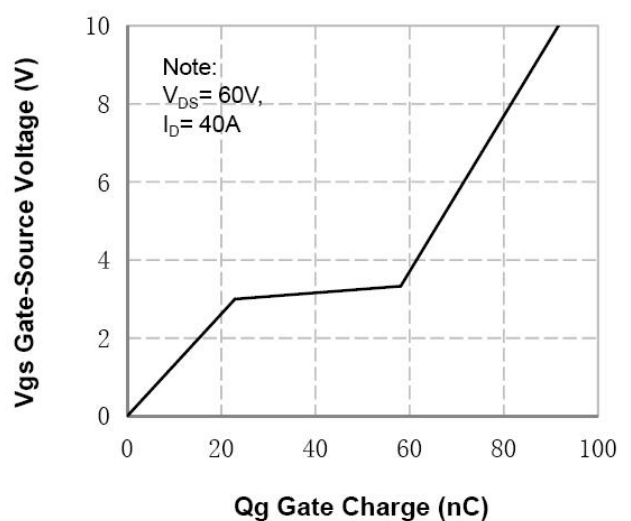


Figure 6. Gate Charge Characteristics

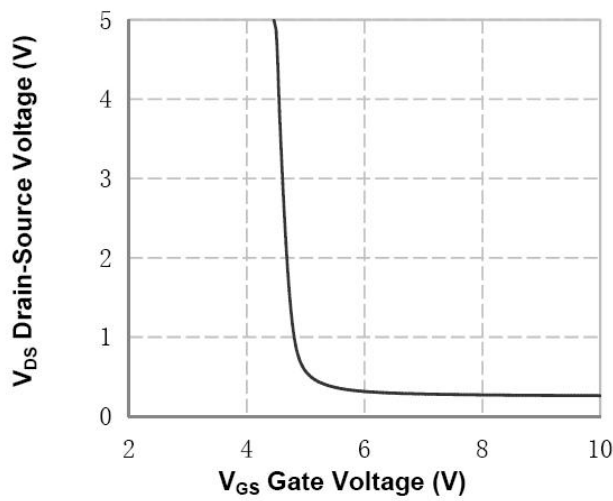


Figure 7. Vds Drain-Source Voltage vs Gate Voltage

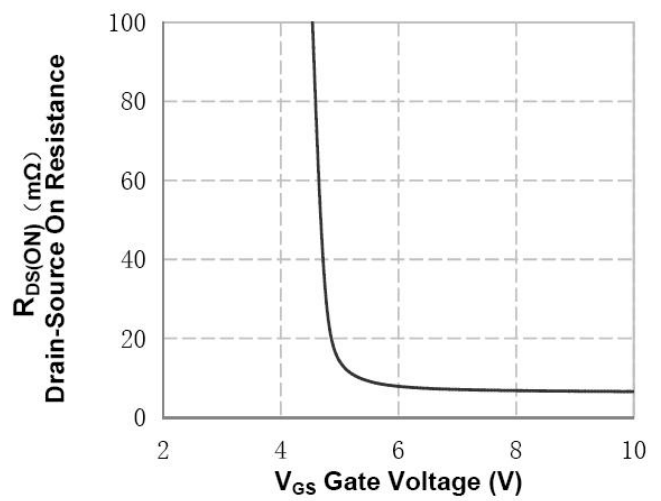


Figure 8. On-Resistance vs Gate Voltage

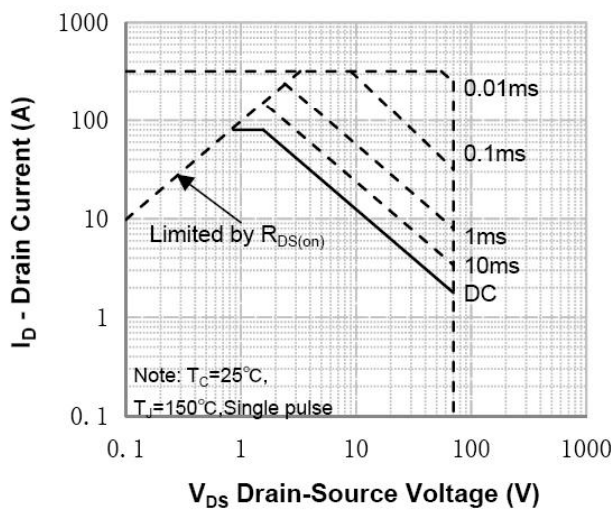


Figure 9. Maximum Safe Operating Area

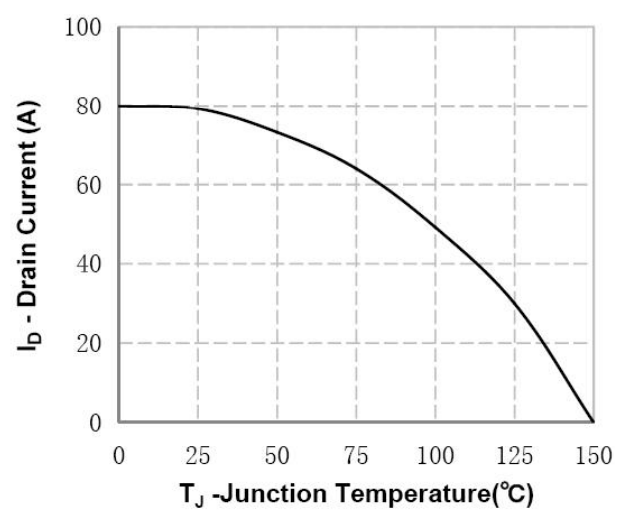


Figure 10. Maximum Continuous Drain Current vs Temperature

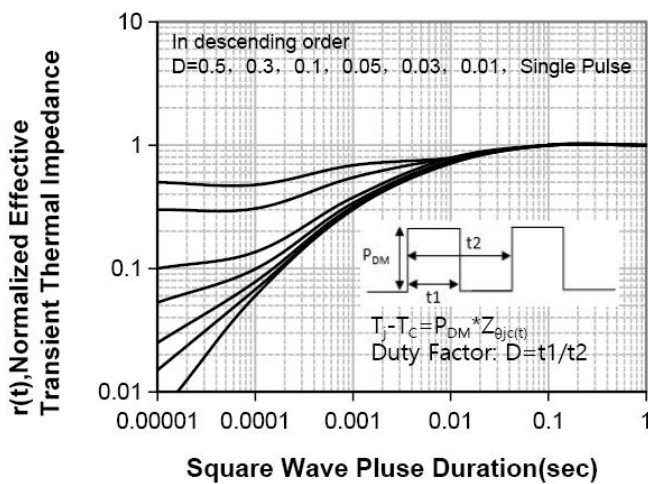
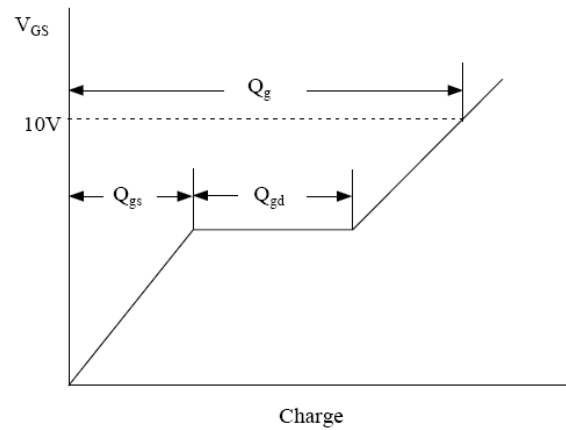
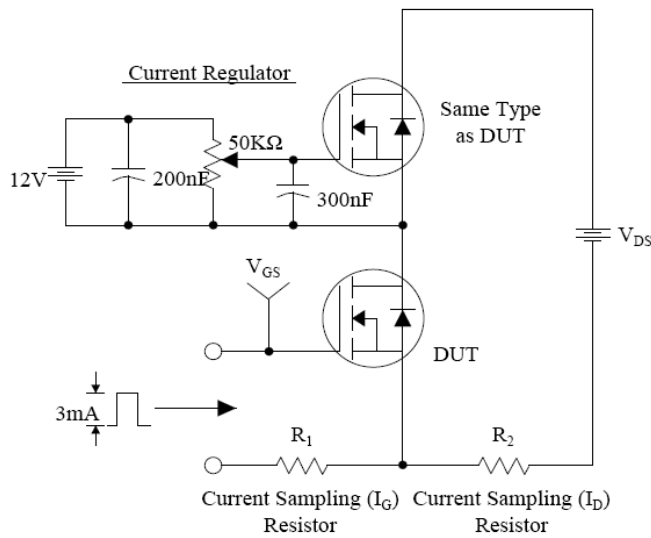


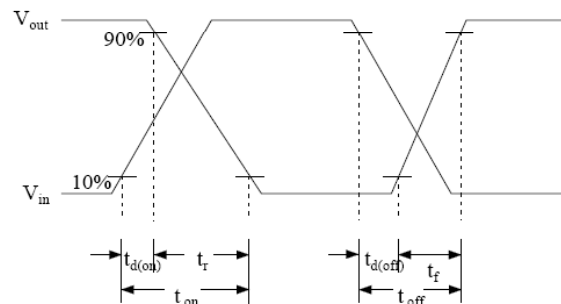
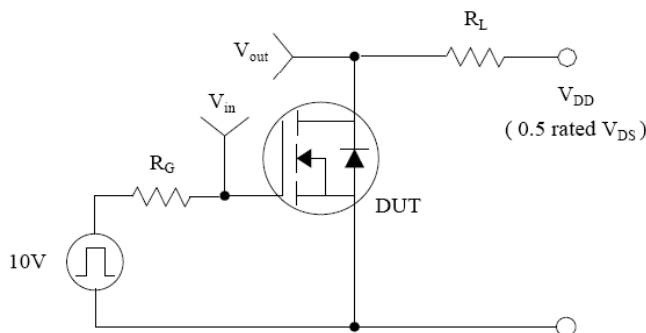
Figure 11. Transient Thermal Response Curve

9. Test Circuits and Waveforms

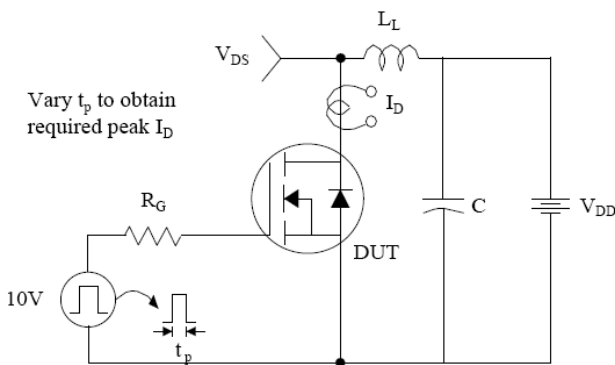
Gate Charge Test Circuit & Waveform



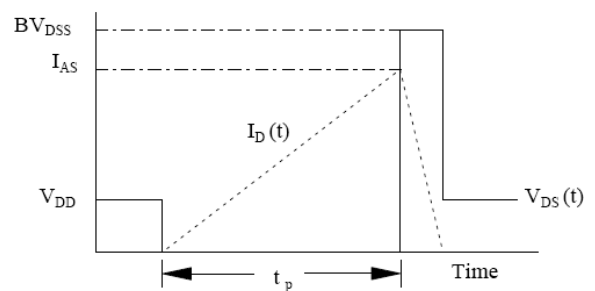
Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching Test Circuit & Waveforms



$$E_{AS} = \frac{1}{2} L_L I_{AS}^2$$



Peak Diode Recovery dv/dt Test Circuit & Waveforms

